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Charvaka Duvvury, Texas Instruments

Seminar #2 – TCAD ESD Simulation Techniques
Kai Esmark, Infineon

Seminar #3 – TLP Theory and Advanced TLP Subjects
Co-copyrighted by ESDA and ThermoFisher Scientific
Evan Grund, Thermo Fisher Scientific

Seminar #4 – HF Constraints and Optimization Criteria for HF/ESD Codesign
Thomas Lee, Stanford University

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Ajith Amerasekera, Texas Instruments

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S. Mitra, R. Gauthier, J. Li, C. Putnam, K. Chatty, R. Halbach, C. Seguin, IBM Microelectronics
Semiconductor Research and Development Center

Presentation 1.2 Thin Gate Oxides Time-to-Breakdown in the ESD Time Domain and Consequences for Applications
A. Ille, Infineon Technologies and Universite de Provence; W. Stadler, H. Gossner, T. Brodbeck, T. Pompl, Infineon Technologies; A. Bravaix, Universite de Provence

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Y. Gao, University Toulouse and ON Semiconductor; N. Guitard, University de Toulouse (now with NXP Semiconductors); M. Bafleur, L. Bary, L. Escotte, Universite de Toulouse; P. Gueulle, L. Lescouzzeres, ON Semiconductor

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M-J Kim, T. Lee, Stanford University; G. Langguth, K. Esmark, H. Gossner, Infineon Technologies AG

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E. Grund, M. Hernandez, Thermo Fisher Scientific

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J. Connor, S. Mitra, G. Wiedemeier, A. Wagstaff, R. Gauthier, M. Muhammad, J. Never, IBM Research and Development Center

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N. Trivedi, L. Chant, P. de Jong T. Smedes, NXP Semiconductors

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B. Keppens, G. Wybo, J. Binnemans, Sarnoff Europe

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S. Marum, D. Wang, A. Chadwick, Texas Instruments

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J. Barth, J. Richner, Barth Electronics, Inc.; L. G. Henry, ESD/TLP Consulting

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T. Lin, J. Chang, Megalin Source International

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E. Grund, ThermoFisher Scientific

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O. Marichal, B. Van Camp, Sarnoff Europe